

## BAS40W SERIES SCHOTTKY DIODE

### FEATURES

Power dissipation

$P_D$ : 200 mW ( $T_{amb}=25^\circ\text{C}$ )

Collector current

$I_F$ : 200 mA

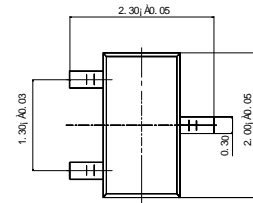
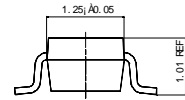
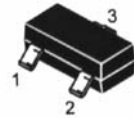
Collector-base voltage

$V_R$ : 40 V

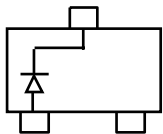
Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$

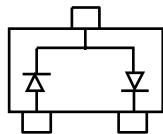
### SOT-323



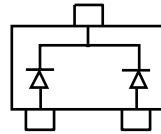
Unit: mm



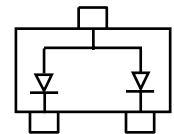
BAS40W Marking: 43.K43



BAS40W-04 Marking: 44.K44



BAS40W-05 Marking: 45.K45



BAS40W-06 Marking: 46.K46

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=10\mu\text{A}$	40		V
Reverse voltage leakage current	$I_R$	$V_R=30\text{V}$		200	nA
Forward voltage	$V_F$	$I_F=1\text{mA}$ $I_F=40\text{mA}$		380 1000	mV
Diode capacitance	$C_D$	$V_R=0\text{V}, f=1\text{MHz}$		5	pF
Reveres recovery time	$t_{rr}$	$I_F=10\text{mA}$ through $I_R=10\text{mA}$ to $I_R=1\text{mA}$		5	nS